

## Maximum Ratings – D1, D2 (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Single phase, half wave, 60Hz, resistive or inductive load.  
For capacitance load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	30	V
Working Peak Reverse Voltage	V <sub>RWM</sub>		
DC Blocking Voltage	V <sub>RM</sub>		
RMS Reverse Voltage	V <sub>R(RMS)</sub>	21	V
Average Rectified Output Current (See Figure 1)	I <sub>O</sub>	3.0	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I <sub>FSM</sub>	20	A

## Maximum Ratings – Q1, Q2 (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Input Voltage Between Two MOSFET Drain	V <sub>LL</sub>	30	V
Drain-Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	I <sub>D</sub>	3.2	A

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	500	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	R <sub>θJA</sub>	250	°C/W
Power Dissipation (Note 6)	P <sub>D</sub>	1000	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	R <sub>θJA</sub>	125	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics – D1, D2 (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 7)	V <sub>(BR)R</sub>	30	—	—	V	I <sub>R</sub> = 400μA
Forward Voltage Drop	V <sub>F</sub>	—	0.25	0.278	V	I <sub>F</sub> = 0.1A, T <sub>J</sub> = +25°C
		—	0.33	0.37		I <sub>F</sub> = 1.0A, T <sub>J</sub> = +25°C
		—	0.36	0.42		I <sub>F</sub> = 2.0A, T <sub>J</sub> = +25°C
		—	0.24	0.27		I <sub>F</sub> = 0.1A, T <sub>J</sub> = +125°C
		—	0.33	0.36		I <sub>F</sub> = 1.0A, T <sub>J</sub> = +125°C
		—	0.35	0.40		I <sub>F</sub> = 2.0A, T <sub>J</sub> = +125°C
Leakage Current (Note 7)	I <sub>R</sub>	—	50	150	μA	V <sub>R</sub> = 5V, T <sub>J</sub> = +25°C
		—	100	400	μA	V <sub>R</sub> = 30V, T <sub>J</sub> = +25°C
		—	6	15	mA	V <sub>R</sub> = 5V, T <sub>J</sub> = +125°C
		—	10	20	mA	V <sub>R</sub> = 30V, T <sub>J</sub> = +125°C

Notes: 5. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at <http://www.diodes.com>.  
6. Part mounted on FR-4 board with 1-in sq pad layout, 2oz Cu.  
7. Short duration pulse test used to minimize self-heating effect. Pulse width ≤ 300μs, duty cycle ≤ 2%.

**Electrical Characteristics – Q1, Q2** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

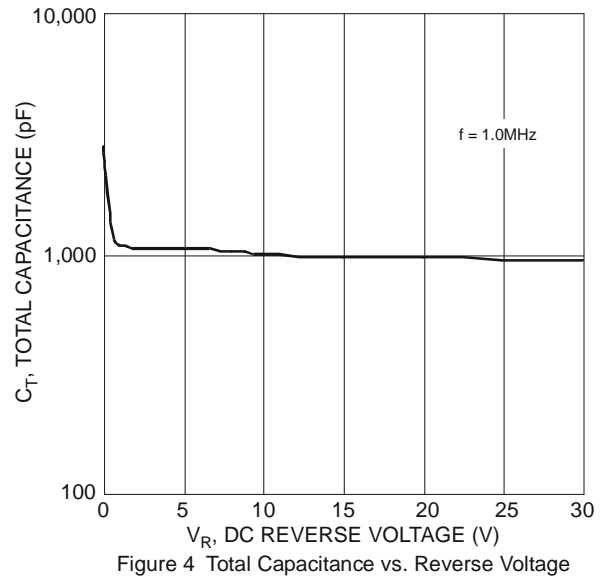
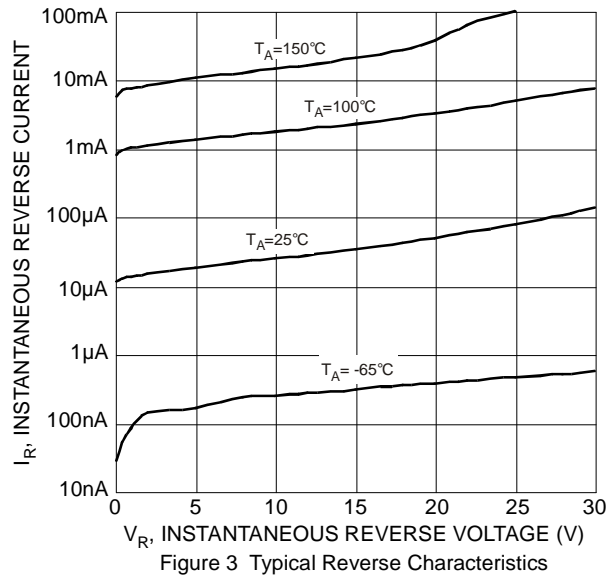
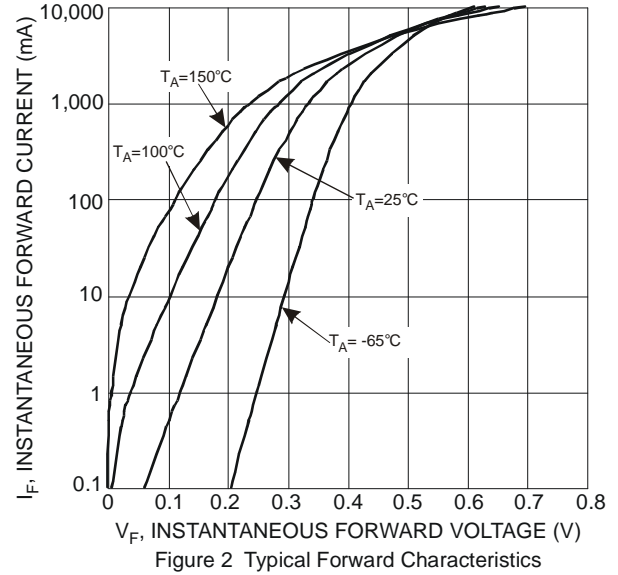
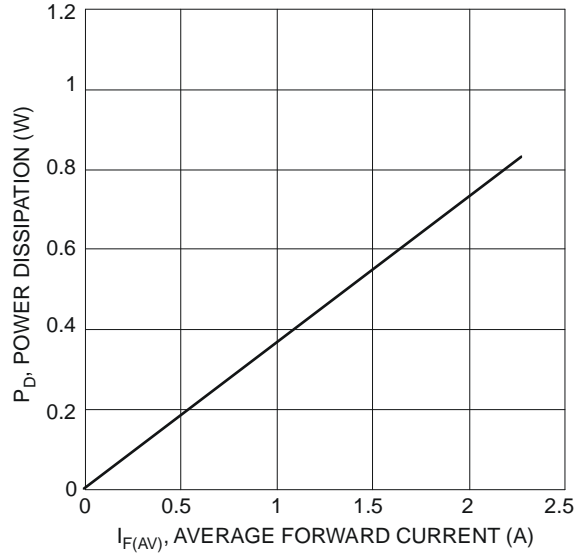
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	220	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±200	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	—	2.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	13	--	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.0A
			17	26		V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.2A
			22	--		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.0A
			23	32		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.2A
Forward Transconductance	g <sub>fs</sub>	—	7	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 2.0A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	0.5	—	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 2.25A

**Electrical Characteristics – DFBR030U3LP** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Rectifying Forward Voltage (Note 7)	V <sub>fd2</sub>	—	0.45	0.56	V	Input voltage V <sub>LL</sub> = ±5V; The output current of Rectifier I <sub>OUT</sub> = 2A
Rectifier leakage current	I <sub>leak</sub>	—	30	1000	μA	Input voltage V <sub>LL</sub> = 16V; No Load on the Rectifier output
Rectifier Reverse leakage current	I <sub>rleak</sub>	—	20	1000	μA	Input voltage V <sub>LL</sub> = 0V; The output voltage of the Rectifier V <sub>OUT</sub> = 5V

Note: 7. Short duration pulse test used to minimize self-heating effect. Pulse width ≤ 300μs, duty cycle ≤ 2%.

## Typical Performance Curves – D1, D2



# Typical Performance Curves – Q1, Q2

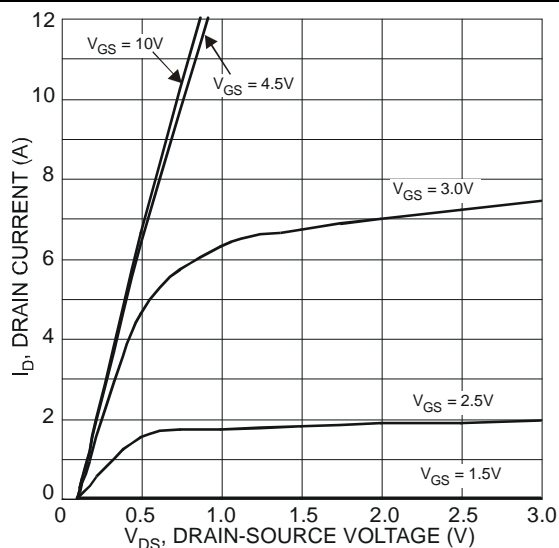


Figure 5 Typical Output Characteristics

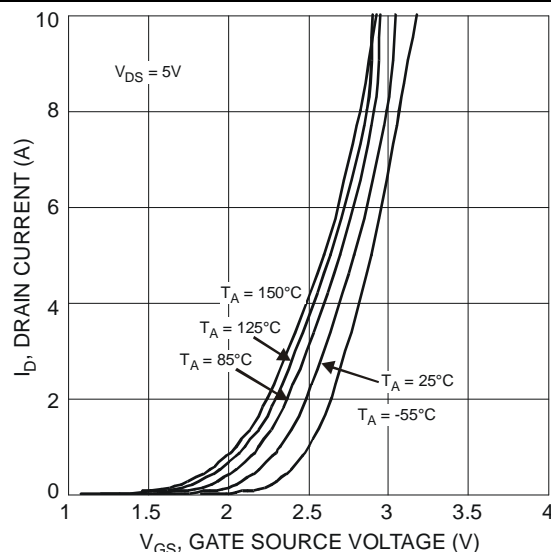


Figure 6 Typical Transfer Characteristics

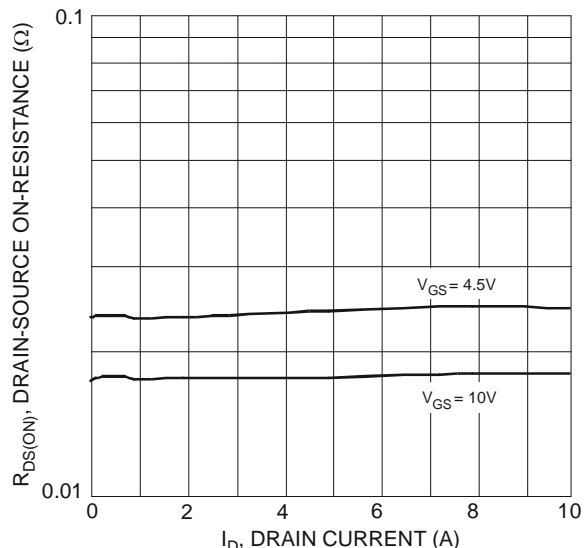


Figure 7 Typical On-Resistance vs. Drain Current and Gate Voltage

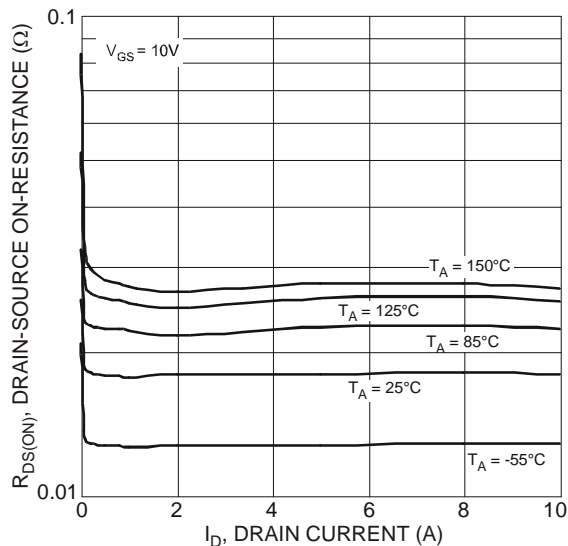


Figure 8 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

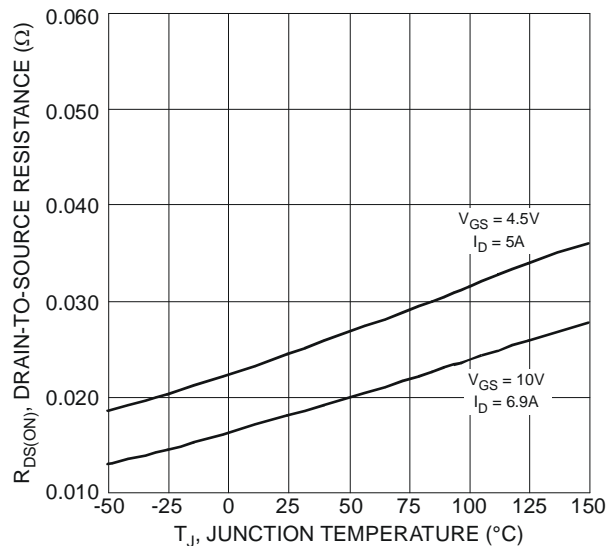


Figure 9 On-Resistance Variation with Temperature

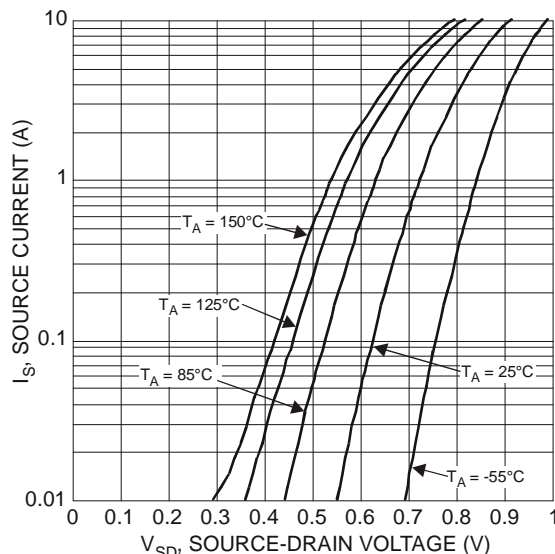


Figure 10 Diode Forward Voltage vs. Current

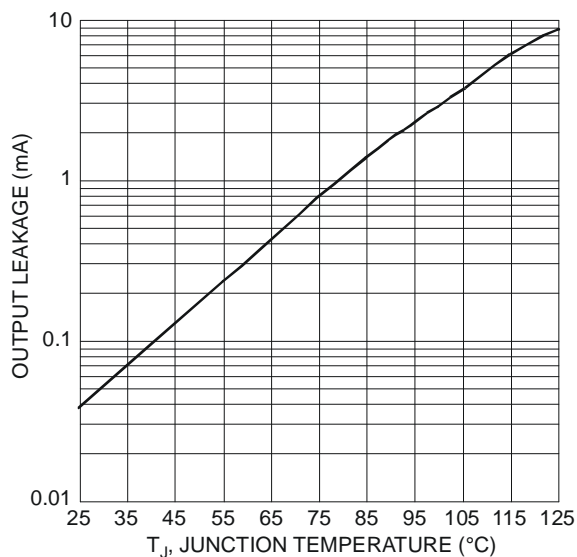


Figure 11 Output Leakage at 5V Bias vs. Junction Temperature

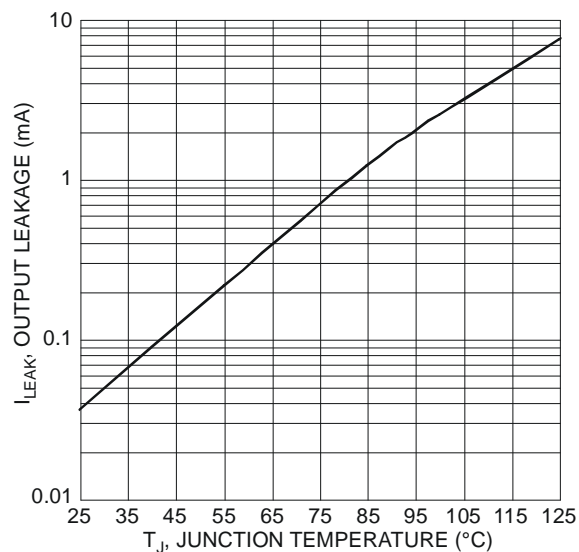


Figure 12 Input Leakage at 16V Bias vs. Junction Temperature

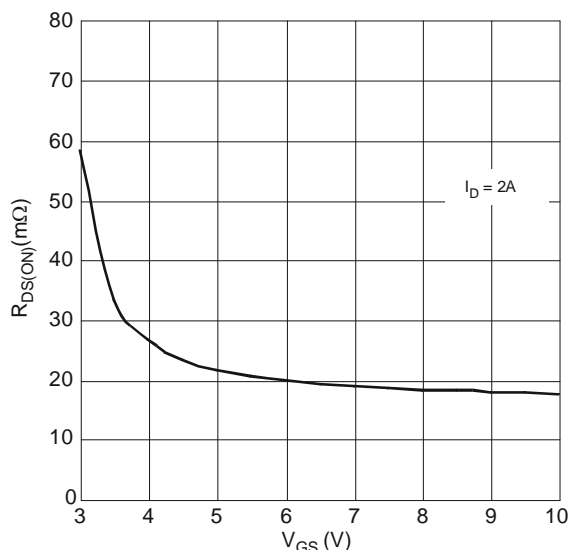


Figure 13 FET Typical On-Resistance vs. Gate-to-Source Voltage (from 3V to 10V)

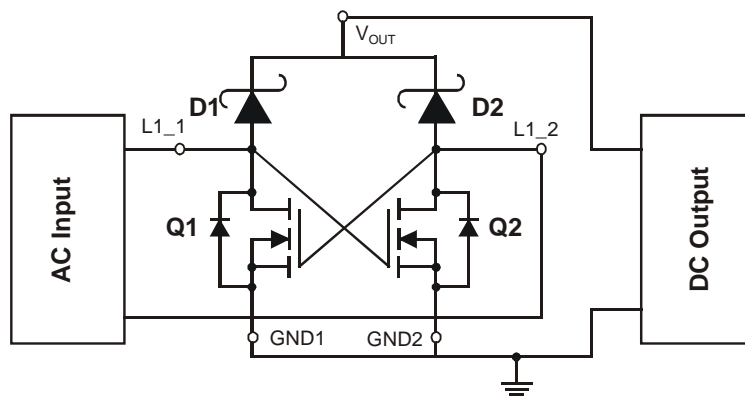
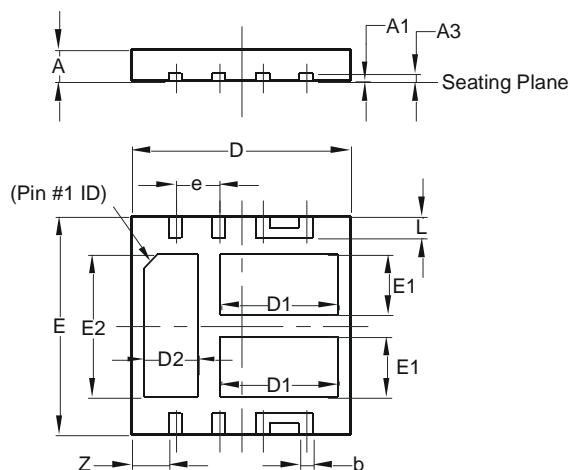


Figure 14 Typical Application Circuit  
GND1 and GND2 are not internally connected.  
The user should make the connection in the PCB design.

## Package Outline Dimensions

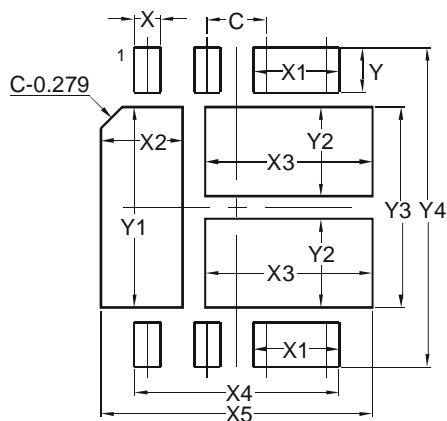
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



U-DFN4040-8			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.02
A3	-	-	0.15
b	0.20	0.30	0.25
D	3.95	4.05	4.00
D1	2.05	2.25	2.15
D2	0.90	1.10	1.00
E	3.95	4.05	4.00
E1	1.00	1.20	1.10
E2	2.50	2.70	2.60
e	-	-	0.80
L	0.35	0.45	0.40
Z	-	-	0.675
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.800
X	0.350
X1	1.150
X2	1.100
X3	2.250
X4	2.750
X5	3.650
Y	0.600
Y1	2.700
Y2	1.200
Y3	2.700
Y4	4.300

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